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(54) Title: PLANE-PARALLEL STRUCTURES OF SILICON/SILICON OXIDE

(57) Abstract: The present invention relates to plane-parallel structures of silicon/silicon oxide (silicon/silicon oxide flakes), obtainable by heating plane-parallel structures of SiO_x in an oxygen-free atmosphere at a temperature above 400 °C, wherein 0.70 ≤ y ≤ 1.8, or plane-parallel structures of silicon/silicon oxide, obtainable by heating plane-parallel structures of SiO_x in an oxygen-free atmosphere at a temperature above 400 °C, wherein 0.03 ≤ x ≤ 0.95, a process for their production and their use for the production of interference pigments.